

MJE170, MJE171, MJE172 (PNP), MJE180, MJE181, MJE182 (NPN)

Preferred Device

Complementary Plastic Silicon Power Transistors

The MJE170/180 series is designed for low power audio amplifier and low current, high speed switching applications.

Features

- Collector–Emitter Sustaining Voltage –
 $V_{CEO(sus)} = 40 \text{ Vdc} - \text{MJE170, MJE180}$
 $= 60 \text{ Vdc} - \text{MJE171, MJE181}$
 $= 80 \text{ Vdc} - \text{MJE172, MJE182}$
- DC Current Gain –
 $h_{FE} = 30 \text{ (Min) @ } I_C = 0.5 \text{ Adc}$
 $= 12 \text{ (Min) @ } I_C = 1.5 \text{ Adc}$
- Current–Gain – Bandwidth Product –
 $f_T = 50 \text{ MHz (Min) @ } I_C = 100 \text{ mAdc}$
- Annular Construction for Low Leakages –
 $I_{CBO} = 100 \text{ nA (Max) @ Rated } V_{CB}$
- Epoxy Meets UL 94 V–0 @ 0.125 in
- ESD Ratings: Machine Model, C
Human Body Model, 3B
- Pb–Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Base Voltage MJE170, MJE180 MJE171, MJE181 MJE172, MJE182	V_{CB}	60 80 100	Vdc
Collector–Emitter Voltage MJE170, MJE180 MJE171, MJE181 MJE172, MJE182	V_{CEO}	40 60 80	Vdc
Emitter–Base Voltage	V_{EB}	7.0	Vdc
Collector Current – Continuous – Peak	I_C	3.0 6.0	Adc
Base Current	I_B	1.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 0.012	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	12.5 0.1	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	$^\circ\text{C}$

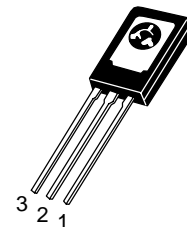
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



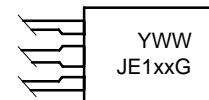
ON Semiconductor®

**3 AMPERES
POWER TRANSISTORS
COMPLEMENTARY SILICON
40 – 60 – 80 VOLTS
12.5 WATTS**



TO–225AA
CASE 77–09
STYLE 1

MARKING DIAGRAM



Y = Year
 WW = Work Week
 JE1xx = Specific Device Code
 x = 70, 71, 72, 80, 81, or 82
 G = Pb–Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

MJE170, MJE171, MJE172 (PNP), MJE180, MJE181, MJE182 (NPN)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θ_{JC}	10	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	θ_{JA}	83.4	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 0$)	MJE170, MJE180 MJE171, MJE181 MJE172, MJE182	$V_{CEO(sus)}$	40 60 80	- -	Vdc
Collector Cutoff Current ($V_{CB} = 60 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 80 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 100 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 60 \text{ Vdc}$, $I_E = 0$, $T_C = 150^{\circ}\text{C}$) ($V_{CB} = 80 \text{ Vdc}$, $I_E = 0$, $T_C = 150^{\circ}\text{C}$) ($V_{CB} = 100 \text{ Vdc}$, $I_E = 0$, $T_C = 150^{\circ}\text{C}$)	MJE170, MJE180 MJE171, MJE181 MJE172, MJE182 MJE170, MJE180 MJE171, MJE181 MJE172, MJE182	I_{CBO}	- - - - -	0.1 0.1 0.1 0.1 0.1	μAdc mAdc
Emitter Cutoff Current ($V_{BE} = 7.0 \text{ Vdc}$, $I_C = 0$)		I_{EBO}	-	0.1	μAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 100 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 500 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 1.5 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$)		h_{FE}	50 30 12	250 -	-
Collector-Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$) ($I_C = 1.5 \text{ Adc}$, $I_B = 150 \text{ mAdc}$) ($I_C = 3.0 \text{ Adc}$, $I_B = 600 \text{ mAdc}$)		$V_{CE(sat)}$	- - -	0.3 0.9 1.7	Vdc
Base-Emitter Saturation Voltage ($I_C = 1.5 \text{ Adc}$, $I_B = 150 \text{ mAdc}$) ($I_C = 3.0 \text{ Adc}$, $I_B = 600 \text{ mAdc}$)		$V_{BE(sat)}$	- -	1.5 2.0	Vdc
Base-Emitter On Voltage ($I_C = 500 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)		$V_{BE(on)}$	-	1.2	Vdc

DYNAMIC CHARACTERISTICS

Current-Gain - Bandwidth Product (Note 1) ($I_C = 100 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f_{test} = 10 \text{ MHz}$)		f_T	50	-	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 0.1 \text{ MHz}$)	MJE171/MJE172 MJE181/MJE182	C_{ob}	- -	60 40	pF

1. $f_T = |h_{fe}| \cdot f_{test}$

MJE170, MJE171, MJE172 (PNP), MJE180, MJE181, MJE182 (NPN)

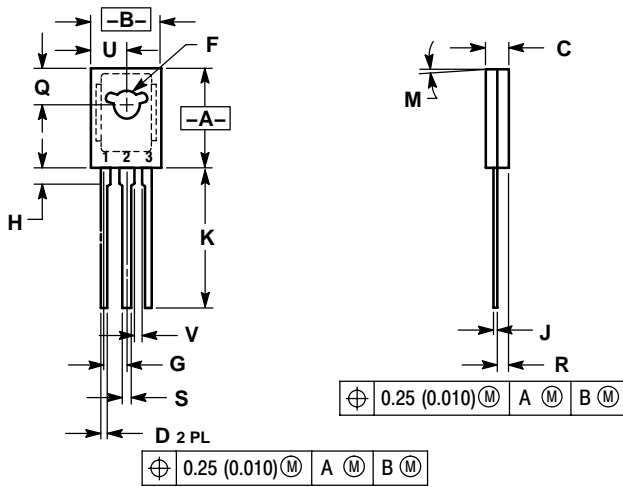
ORDERING INFORMATION

Device	Package	Shipping
MJE170	TO-225	500 Units / Box
MJE170G	TO-225 (Pb-Free)	
MJE171	TO-225	
MJE171G	TO-225 (Pb-Free)	
MJE172	TO-225	
MJE172G	TO-225 (Pb-Free)	
MJE180	TO-225	
MJE180G	TO-225 (Pb-Free)	
MJE181	TO-225	
MJE181G	TO-225 (Pb-Free)	
MJE182	TO-225	
MJE182G	TO-225 (Pb-Free)	

MJE170, MJE171, MJE172 (PNP), MJE180, MJE181, MJE182 (NPN)

PACKAGE DIMENSIONS

TO-225
CASE 77-09
ISSUE Z



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 1:

- PIN 1. EMITTER
2. COLLECTOR
3. BASE